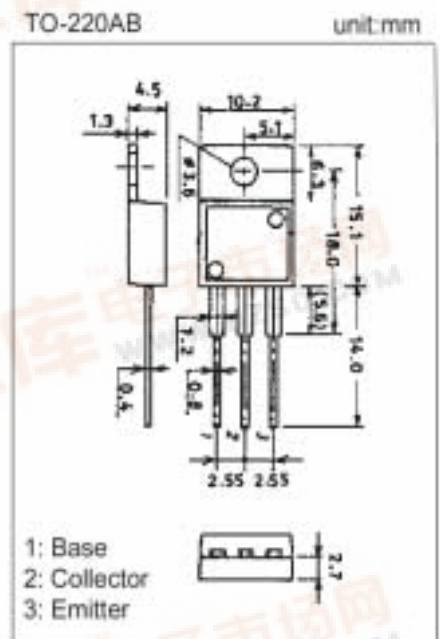




CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	VCBO	700	V
Collector-Emitter Voltage	VCEO	400	V
Emitter-Base Voltage	VEBO	9	V
Collector Current	Ic	4	A
Collector Power Dissipation	Ptot		
Junction Temperature	Tj	150	°C
Storage Temperature Range	Tstg	-55~+150	°C



CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	MAX.	UNIT
Collector-Emitter Sustaining Voltage		Ic=1mA, IB=0	400	-	V
Collector-Base Breakdown Voltage	V(BR)CBO	IE=0, Ic=1mA	700	-	V
Emitter-Base Breakdown Voltage	V(BR) EBO	IE=1mA, IC=0	9	-	V
Collector Cut off current	ICBO	VCB=700V, IE=0	-	∞	μ A
Collector-Emitter Cut off Current	ICEO	VCE=400V, IB=0	-		μ A
Emitter-Base Cut off Voltage	IEBO	VEB=9V, Ic=0	-		μ A
DC Current Gain	hFE	VCE=			
Collector-Emitter Saturation Voltage	VCE(sat)	Ic=1A, IB=0.25A	-		
Base-Emitter Saturation Voltage	VBE(sat)	Ic=			
Fall Time	tf	Ic=2A		.9	μ S
Storage Time	ts	IB1=- IB2=0.4A	-	4	μ S
Frequency Characteristics	fT	VCE=10V, Ic=0.5A, f=1MHz	5	-	MHz